PRELIMINARY

CY14B104L/CY14B104N

4-Mbit (512K x 8/256K x 16) nvSRAM

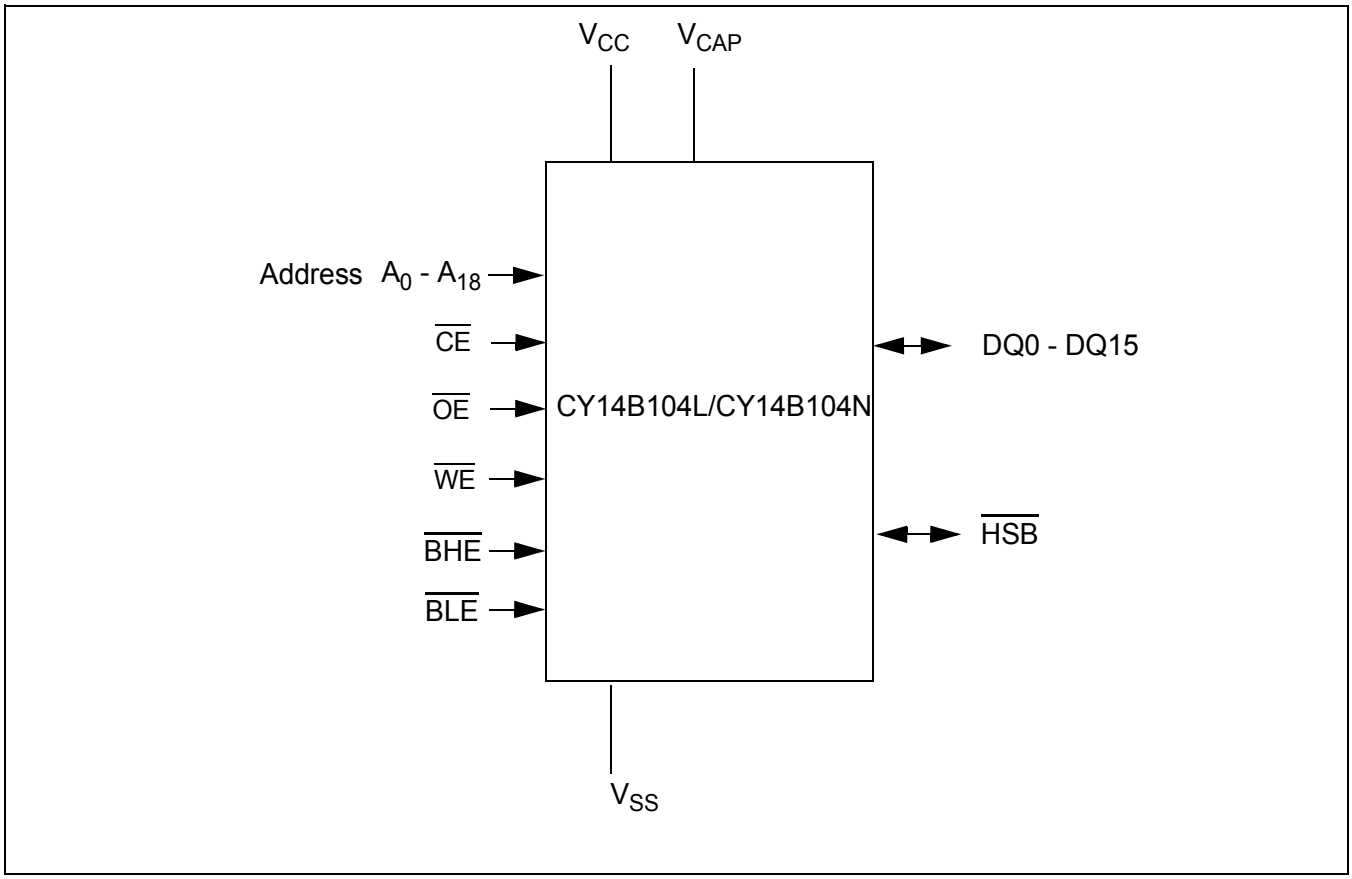
Feature

- 15 ns, 25 ns, and 45 ns access times
- Internally organized as 512K x 8 or 256K x 16
- Hands-off automatic *STORE* on power down with only a small capacitor
- *STORE* to *QuantumTrap*® nonvolatile elements is initiated by software, device pin or Autostore® on power down
- *RECALL* to SRAM initiated by software or power up
- Infinite read, write, and recall cycles
- 8 mA typical I_{CC} at 200 ns cycle time
- 200,000 *STORE* cycles to *QuantumTrap*
- 20 year data retention
- Single 3V +20%, –10% operation
- Commercial and industrial temperatures
- FBGA and TSOP - II packages
- RoHS compliance

Functional Description

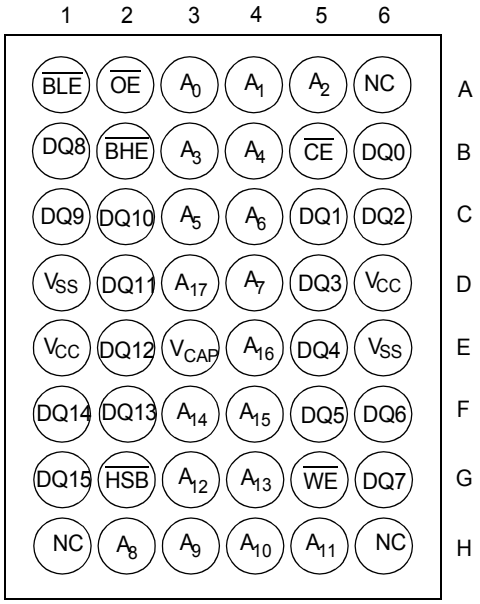
The Cypress CY14B104L/CY14B104N is a fast static RAM, with a nonvolatile element in each memory cell. The memory is organized as 512K words of 8 bits each or 256K words of 16 bits each. The embedded nonvolatile elements incorporate QuantumTrap technology producing the world's most reliable nonvolatile memory. The SRAM provides infinite read and write cycles, while independent, nonvolatile data resides in the highly reliable QuantumTrap cell. Data transfers from the SRAM to the nonvolatile elements (the STORE operation) takes place automatically at power down. On power up, data is restored to the SRAM (the RECALL operation) from the nonvolatile memory. Both the STORE and RECALL operations are also available under software control.

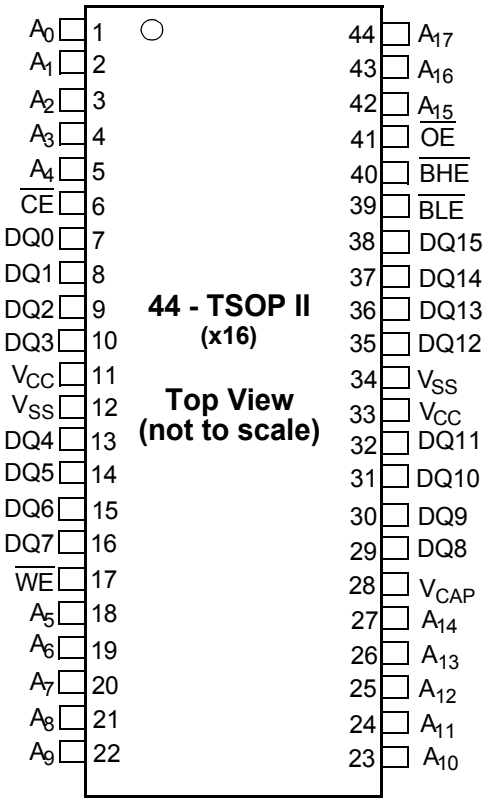
Logic Block Diagram



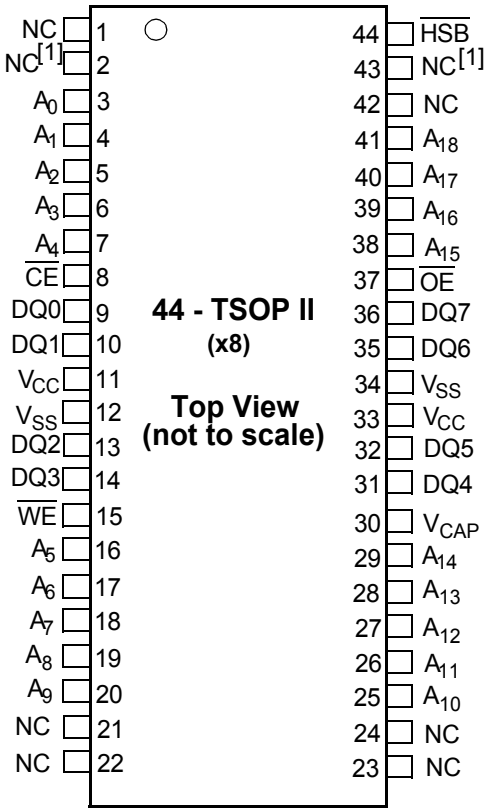
Pin Configurations

48 - FBGA
(x16)
Top View
(not to scale)





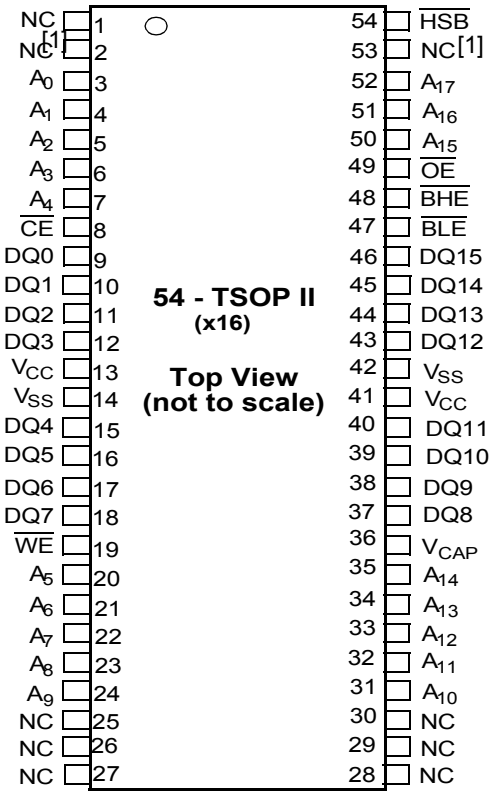
44 - TSOP II
(x16)
Top View
(not to scale)



44 - TSOP II
(x8)
Top View
(not to scale)

Note
1. Expandable to 8Mbit,16Mbit

Pin Configurations (continued)



Pin Definitions

Pin Name	IO Type	Description
$A_0 – A_{16}$	Input	**Address Inputs used to select one of the 131,072 bytes of the nvSRAM**.
DQ0 – DQ7	Input Output	**Bidirectional Data IO Lines**. Used as input or output lines depending on operation.
$\overline{WE}$	Input	**Write Enable Input, Active LOW**. When selected LOW, enables data on the IO pins to be written to the address location latched by the falling edge of $\overline{CE}$.
$\overline{CE}$	Input	**Chip Enable Input, Active LOW**. When LOW, selects the chip. When HIGH, deselects the chip.
$\overline{OE}$	Input	**Output Enable, Active LOW**. The active LOW $\overline{OE}$ input enables the data output buffers during read cycles. IO pins are tri-stated on deasserting $\overline{OE}$ high.
V_{SS}	Ground	**Ground For The Device.** Must be connected to ground of the system.
V_{CC}	Power Supply	**Power Supply Inputs To The Device**.
$\overline{HSB}$	Input Output	**Hardware Store Busy (HSB)**. When low this output indicates a hardware store is in progress. When pulled low external to the chip it initiates a nonvolatile STORE operation. A weak internal pull up resistor keeps this pin HIGH if not connected. (connection optional)
V_{CAP}	Power Supply	**Autostore Capacitor**. Supplies power to nvSRAM during power loss to store data from SRAM to nonvolatile elements.
NC	No Connect	**No Connect**. Do not connect this pin to the die.

Device Operation

The CY14B104L/CY14B104N nvSRAM is made up of two functional components paired in the same physical cell. They are an SRAM memory cell and a nonvolatile QuantumTrap cell. The SRAM memory cell operates as a standard fast static RAM. Data in the SRAM can be transferred to the nonvolatile cell (the STORE operation), or from the nonvolatile cell to SRAM (the RECALL operation). This unique architecture allows all cells to be stored and recalled in parallel.During the STORE and RECALL operations SRAM read and write operations are inhibited. The CY14B104L/CY14B104N suports infinite reads and writes just like a typical SRAM.In addition,it provides infinite RECALL operations from the nonvolatile cells and up to 200K STORE operations.

SRAM Read

The CY14B104L/CY14B104N performs a READ cycle whenever $\overline{CE}$ and $\overline{OE}$ are LOW while $\overline{WE}$ and $\overline{HSB}$ are HIGH. The address specified on pins A_{0-18}/A_{0-17} determines which of the 524,288 data bytes or 262,144 words of 16 bits each will be accessed. When the read is initiated by an address transition, the outputs will be valid after a delay of t_{AA} (read cycle #1). If the read is initiated by $\overline{CE}$ or $\overline{OE}$, the outputs will be valid at t_{ACE} or at t_{DOE}, whichever is later (read cycle #2). The data outputs will repeatedly respond to address changes within the t_{AA} access time without the need for transitions on any control input pins, and will remain valid until another address change or until $\overline{CE}$ or $\overline{OE}$ is brought HIGH, or $\overline{WE}$ or $\overline{HSB}$ is brought LOW.

SRAM Write

A WRITE cycle is performed whenever $\overline{CE}$ and $\overline{WE}$ are low and $\overline{HSB}$ is high. The address inputs must be stable prior to entering the WRITE cycle and must remain stable until either $\overline{CE}$ or $\overline{WE}$ goes high at the end of the cycle. The data on the common IO pins $DQ_{0–15}$ will be written into the memory if the data is valid t_{SD} before the end of a $\overline{WE}$ controlled WRITE or before the end of an $\overline{CE}$ controlled WRITE. It is recommended that $\overline{OE}$ kept high during the entire WRITE cycle to avoid data bus contention on common IO lines. If $\overline{OE}$ is left low, internal circuitry turns off the output buffers t_{HZWE} after $\overline{WE}$ goes low.

AutoStore Operation

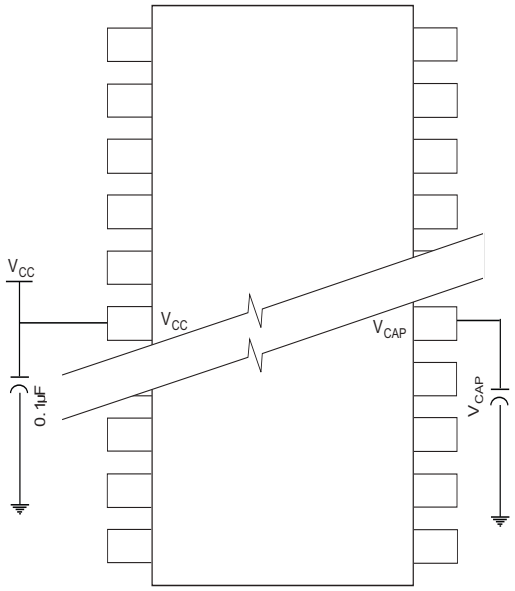
The CY14B104L/CY14B104N stores data to nvSRAM using one of the three storage operations. These three operations are Hardware Store activated by $\overline{HSB}$, Software Store activated by an address sequence, and AutoStore on device power down. AutoStore operation is a unique feature of QuantumTrap technology and is enabled by default on the CY14B104L/CY14B104N.

During normal operation, the device draws current from V_{CC} to charge a capacitor connected to the V_{CAP} pin. This stored charge will be used by the chip to perform a single STORE operation. If the voltage on the V_{CC} pin drops below V_{SWITCH}, the part automatically disconnects the V_{CAP} pin from V_{CC}. A STORE operation will be initiated with power provided by the V_{CAP} capacitor.

Figure 1shows the proper connection of the storage capacitor (V_{CAP}) for automatic store operation. Refer to the DC Electrical Characteristics on page 8 for the size of V_{CAP}.

To reduce unnecessary nonvolatile stores, AutoStore, and Hardware Store operations will be ignored unless at least one WRITE operation has taken place since the most recent STORE or RECALL cycle. Software initiated STORE cycles are performed regardless of whether a WRITE operation has taken place. Monitor the $\overline{HSB}$ signal by the system to detect if an AutoStore cycle is in progress.

Figure 1. AutoStore Mode



Hardware STORE Operation

The CY14B104L/CY14B104N provides the $\overline{HSB}$ pin for controlling and acknowledging the STORE operations. Use the $\overline{HSB}$ pin to request a hardware STORE cycle. When the $\overline{HSB}$ pin is driven low, the CY14B104L/CY14B104N conditionally initiates a STORE operation after t_{DELAY}. An actual STORE cycle only begins if a WRITE to the SRAM took place since the last STORE or RECALL cycle. The $\overline{HSB}$ pin also acts as an open drain driver that is internally driven low to indicate a busy condition while the STORE (initiated by any means) is in progress.

SRAM READ and WRITE operations that are in progress when $\overline{HSB}$ is driven low by any means are given time to complete before the STORE operation is initiated. After $\overline{HSB}$ goes low, the CY14B104L/CY14B104N continues SRAM operations for t_{DELAY}. During t_{DELAY}, multiple SRAM READ operations may take place. If a WRITE is in progress when $\overline{HSB}$ is pulled low it will be allowed a time, t_{DELAY} to complete. However, any SRAM WRITE cycles requested after $\overline{HSB}$ goes low will be inhibited until $\overline{HSB}$ returns high.

During any STORE operation, regardless of how it was initiated, the CY14B104L/CY14B104N continues to drive the $\overline{HSB}$ pin low, releasing it only when the STORE is complete.

Upon completion of the STORE operation the CY14B104L/CY14B104N remains disabled until the HSB pin returns high. Leave the HSB unconnected if is not used.

Hardware RECALL (Power Up)

During power up or after any low power condition (V_{CC}< V_{SWITCH}), an internal RECALL request will be latched. When V_{CC} once again exceeds the sense voltage of V_{SWITCH}, a RECALL cycle will automatically be initiated and takes $t_{HRECALL}$ to complete.

Software STORE

Transfer data from the SRAM to the nonvolatile memory with a software address sequence. The CY14B104L/CY14B104N software STORE cycle is initiated by executing sequential CE-controlled READ cycles from six specific address locations in exact order. During the STORE cycle an erase of the previous nonvolatile data is first performed, followed by a program of the nonvolatile elements. Once a STORE cycle is initiated, further input and output are disabled until the cycle is completed.

Because a sequence of READs from specific addresses is used for STORE initiation, it is important that no other READ or WRITE accesses intervene in the sequence. If there are intervening READ or WRITE accesses, the sequence will be aborted and no STORE or RECALL takes place.

To initiate the software STORE cycle, the following READ sequence must be performed:

1. Read Address 0x4E38 Valid READ
2. Read Address 0xB1C7 Valid READ
3. Read Address 0x83E0 Valid READ
4. Read Address 0x7C1F Valid READ
5. Read Address 0x703F Valid READ
6. Read Address 0x8FC0 Initiate STORE Cycle

The software sequence may be clocked with CE controlled READs or OE controlled READs. Once the sixth address in the sequence has been entered, the STORE cycle commences and the chip will be disabled. It is important that READ cycles and not WRITE cycles be used in the sequence, although it is not necessary that OE be low for the sequence to be valid. After the t_{STORE} cycle time has been fulfilled, the SRAM will again be activated for READ and WRITE operation.

Software RECALL

Transfer the data from the nonvolatile memory to the SRAM by a software address sequence. A software RECALL cycle is initiated with a sequence of READ operations in a manner similar to the software STORE initiation. To initiate the RECALL cycle, the following sequence of CE controlled READ operations must be performed:

1. Read Address 0x4E38 Valid READ
2. Read Address 0xB1C7 Valid READ
3. Read Address 0x83E0 Valid READ
4. Read Address 0x7C1F Valid READ
5. Read Address 0x703F Valid READ
6. Read Address 0x4C63 Initiate RECALL Cycle

Internally, RECALL is a two-step procedure. First, the SRAM data is cleared and second, the nonvolatile information is transferred into the SRAM cells. After the t_{RECALL} cycle time the SRAM will once again be ready for READ and WRITE operations. The RECALL operation does not alter the data in the nonvolatile elements.

Table 1. Mode Selection

$\overline{CE}$	$\overline{WE}$	$\overline{OE}$	A15 - A0	Mode	IO	Power
H	X	X	X	Not Selected	Output High Z	Standby
L	H	L	X	Read SRAM	Output Data	Active
L	L	X	X	Write SRAM	Input Data	Active
L	H	L	0x4E38 0xB1C7 0x83E0 0x7C1F 0x703F 0x8B45	Read SRAM Read SRAM Read SRAM Read SRAM Read SRAM Autostore Disable	Output Data Output Data Output Data Output Data Output Data Output Data	Active [2,3,4]
L	H	L	0x4E38 0xB1C7 0x83E0 0x7C1F 0x703F 0x4B46	Read SRAM Read SRAM Read SRAM Read SRAM Read SRAM Autostore Enable	Output Data Output Data Output Data Output Data Output Data Output Data	Active [2,3,4]
L	H	L	0x4E38 0xB1C7 0x83E0 0x7C1F 0x703F 0x8FC0	Read SRAM Read SRAM Read SRAM Read SRAM Read SRAM Nonvolatile Store	Output Data Output Data Output Data Output Data Output Data Output High Z	Active I_{CC2} [2,3,4]
L	H	L	0x4E38 0xB1C7 0x83E0 0x7C1F 0x703F 0x4C63	Read SRAM Read SRAM Read SRAM Read SRAM Read SRAM Nonvolatile Recall	Output Data Output Data Output Data Output Data Output Data Output High Z	Active [2,3,4]

Preventing AutoStore

The AutoStore function can be disabled by initiating an AutoStore disable sequence. A sequence of read operations is performed in a manner similar to the software STORE initiation. To initiate the AutoStore disable sequence, the following sequence of $\overline{CE}$ controlled read operations must be performed:

1. Read address 0x4E38 Valid READ
2. Read address 0xB1C7 Valid READ
3. Read address 0x83E0 Valid READ
4. Read address 0x7C1F Valid READ
5. Read address 0x703F Valid READ
6. Read address 0x8B45 AutoStore Disable

The AutoStore can be re-enabled by initiating an AutoStore enable sequence. A sequence of read operations is performed in a manner similar to the software RECALL initiation. To initiate the AutoStore enable sequence, the following sequence of $\overline{CE}$ controlled read operations must be performed:

1. Read address 0x4E38 Valid READ
2. Read address 0xB1C7 Valid READ
3. Read address 0x83E0 Valid READ
4. Read address 0x7C1F Valid READ
5. Read address 0x703F Valid READ
6. Read address 0x4B46 AutoStore Enable

If the AutoStore function is disabled or re-enabled a manual STORE operation (hardware or software) must be issued to save the AutoStore state through subsequent power down cycles. The part comes from the factory with AutoStore enabled.

Notes
2. The six consecutive address locations must be in the order listed. $\overline{WE}$ must be HIGH during all six cycles to enable a nonvolatile cycle.
3. While there are 19 address lines on the CY14B104L/CY14B104N, only the lower 16 lines are used to control software modes.
4. IO state depends on the state of $\overline{OE}$. The IO table shown assumes $\overline{OE}$ LOW.

Data Protection

The CY14B104L/CY14B104N protects data from corruption during low-voltage conditions by inhibiting all externally initiated STORE and write operations. The low voltage condition is detected when V_{CC} < V_{SWITCH}. If the CY14B104L/CY14B104N is in a write mode (both $\overline{CE}$ and $\overline{WE}$ low) at power up, after a RECALL, or after a STORE, the write will be inhibited until a negative transition on $\overline{CE}$ or $\overline{WE}$ is detected. This protects against inadvertent writes during power up or brown out conditions.

Noise Considerations

Refer CY Application Note AN1064.

Maximum Ratings

Exceeding the maximum ratings may impair the useful life of the device.

Storage Temperature ..... –65°C to +150°C

Ambient Temperature with Power Applied ..... –55°C to +150°C

Supply Voltage on V_{CC} Relative to GND ..... –0.5V to 4.1V

Voltage Applied to Outputs in High-Z State ..... –0.5V to V_{CC} + 0.5V

Input Voltage ..... –0.5V to Vcc+0.5V

Transient Voltage (<20 ns) on Any Pin to Ground Potential ..... –2.0V to V_{CC} + 2.0V

Package Power Dissipation Capability (T_A = 25°C) 1.0W

Surface Mount Pb Soldering Temperature (3 Seconds) ..... +260°C

Output Short Circuit Current [5] ..... 15 mA

Static Discharge Voltage ..... > 2001V (per MIL-STD-883, Method 3015)

Latch-up Current ..... > 200 mA

Operating Range

Range	Ambient Temperature	V_{CC}
Commercial	0°C to +70°C	2.7V to 3.6V
Industrial	–40°C to +85°C	2.7V to 3.6V

Above table contains advanced information.

DC Electrical Characteristics

Over the Operating Range (V_{CC} = 2.7V to 3.6V)[6]

Parameter	Description	Test Conditions		Min	Max	Unit
I_{CC1}	Average V_{CC} Current	t_{AVAV} = 15 ns t_{AVAV} = 25 ns t_{AVAV} = 45 ns Dependent on output loading and cycle rate.Values obtained without output loads. I_{OUT} = 0 mA	Commercial		70 65 50	mA mA mA
			Industrial		75 70 52	mA mA mA
I_{CC2}	Average V_{CC} Current during STORE	All Inputs Don't Care, V_{CC} = Max Average current for duration t_{STORE}			3	mA
I_{CC3}	Average V_{CC} Current at t_{AVAV} = 200 ns, 3V, 25°C typical	$\overline{WE}$ > (V_{CC} – 0.2). All other I/P cycling. Dependent on output loading and cycle rate. Values obtained without output loads.			25	mA
I_{CC4}	Average V_{CAP} Current during AutoStore Cycle	All Inputs Don't Care, V_{CC} = Max Average current for duration t_{STORE}			3	mA
I_{SB}	V_{CC} Standby Current	$\overline{CE}$ > (V_{CC} – 0.2). All others V_{IN} < 0.2V or > (V_{CC} – 0.2V). Standby current level after nonvolatile cycle is complete. Inputs are static. f = 0 MHz.			1	mA
I_{IX}	Input Leakage Current	V_{CC} = Max, $V_{SS} \le V_{IN} \le V_{CC}$		–1	+1	µA
I_{OZ}	Off-State Output Leakage Current	V_{CC} = Max, $V_{SS} \le V_{IN} \le V_{CC}$, $\overline{CE}$ or $\overline{OE}$ > V_{IH}		–1	+1	µA
V_{IH}	Input HIGH Voltage			2.0	V_{CC} + 0.5	V
V_{IL}	Input LOW Voltage			V_{CC} – 0.5	0.8	V
V_{OH}	Output HIGH Voltage	I_{OUT} = –2 mA		2.4		V
V_{OL}	Output LOW Voltage	I_{OUT} = 4 mA			0.4	V
V_{CAP}	Storage Capacitor	Between V_{CAP} pin and V_{SS}, 5V Rated		35	57	µF

Capacitance [7]

Parameter	Description	Test Conditions	Max	Unit
C_{IN}	Input Capacitance	T_A = 25°C, f = 1 MHz, V_{CC} = 0 to 3.0V	7	pF
C_{OUT}	Output Capacitance		7	pF

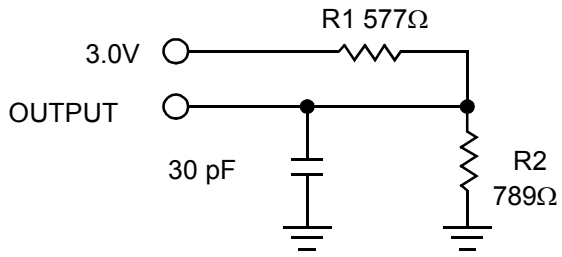
Notes

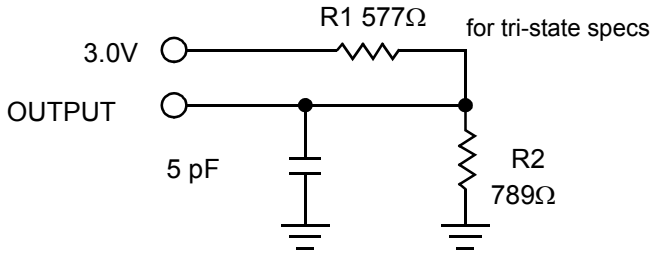
5. Outputs shorted for no more than one second. No more than one output shorted at a time.
6. Typical conditions for the active current shown on the front page of the data sheet are average values at 25°C (room temperature), and V_{CC} = 3V. Not 100% tested.
7. These parameters are guaranteed but not tested.

Thermal Resistance[7]

Parameter	Description	Test Conditions	48-FBGA	44-TSOP II	54-TSOP II	Unit
Θ_{JA}	Thermal Resistance (Junction to Ambient)	Test conditions follow standard test methods and procedures for measuring thermal impedance, in accordance with EIA/JESD51.	TBD	TBD	TBD	°C/W
Θ_{JC}	Thermal Resistance (Junction to Case)		TBD	TBD	TBD	°C/W

AC Test Loads





AC Test Conditions

Input Pulse Levels ..... 0V to 3V
Input Rise and Fall Times (10% - 90%) ..... <5 ns
Input and Output Timing Reference Levels 1.5V

AC Switching Characteristics

Parameters		Description	15ns		25ns		45ns		Unit
Cypress Parameters	Alt. Parameters		Min	Max	Min	Max	Min.	Max.	
SRAM Read Cycle									
t_{ACE}	t_{ACS}	Chip Enable Access Time		15		25		45	ns
t_{RC}[8]	t_{RC}	Read Cycle Time	15		25		45		ns
t_{AA}[9]	t_{AA}	Address Access Time		15		25		45	ns
t_{DOE}	t_{OE}	Output Enable to Data Valid		10		12		20	ns
t_{OHA}	t_{OH}	Output Hold After Address Change	3		3		3		ns
t_{LZCE}[10]	t_{LZ}	Chip Enable to Output Active	3		3		3		ns
t_{HZCE}[10]	t_{HZ}	Chip Disable to Output Inactive		7		10		15	ns
t_{LZOE}[10]	t_{OLZ}	Output Enable to Output Active	0		0		0		ns
t_{HZOE}[10]	t_{OHZ}	Output Disable to Output Inactive		7		10		15	ns
t_{PU}[7]	t_{PA}	Chip Enable to Power Active	0		0		0		ns
t_{PD}[7]	t_{PS}	Chip Disable to Power Standby		15		25		45	ns
t_{DBE}	-	Byte Enale to Data Valid		10		12		22	ns
t_{LZBE}	-	Byte Enable to Output Active	0		0		0		ns
t_{HZBE}	-	Byte Disable to Output Inactive		7		10		22	ns
SRAM Write Cycle									
t_{WC}	t_{WC}	Write Cycle Time	15		25		45		ns
t_{PWE}	t_{WP}	Write Pulse Width	10		20		30		ns
t_{SCE}	t_{CW}	Chip Enable To End of Write	15		20		30		ns
t_{SD}	t_{DW}	Data Setup to End of Write	5		10		15		ns
t_{HD}	t_{DH}	Data Hold After End of Write	0		0		0		ns
t_{AW}	t_{AW}	Address Setup to End of Write	15		20		30		ns
t_{SA}	t_{AS}	Address Setup to Start of Write	0		0		0		ns
t_{HA}	t_{WR}	Address Hold After End of Write	0		0		0		ns
t_{HZWE}[10,11]	t_{WZ}	Write Enable to Output Disable		7		10		15	ns
t_{LZWE}[10]	t_{OW}	Output Active after End of Write	3		3		3		ns
t_{BW}	-	Byte Enable to End of Write	15		20		30		ns

Notes
8. $\overline{WE}$ must be HIGH during SRAM read cycles.
9. Device is continuously selected with $\overline{CE}$ and $\overline{OE}$ both LOW.
10. Measured ±200 mV from steady state output voltage.
11. If $\overline{WE}$ is LOW when $\overline{CE}$ goes LOW, the outputs remain in the high impedance state.

AutoStore/Power Up RECALL

Parameters	Description	CY14B104L/CY14B104N		Unit
		Min	Max	
$t_{HRECALL}$ [12]	Power Up RECALL Duration		20	ms
t_{STORE} [13]	STORE Cycle Duration		15	ms
V_{SWITCH}	Low Voltage Trigger Level		2.65	V
$t_{VCCRISE}$	VCC Rise Time	150		µs

Software Controlled STORE/RECALL Cycle [14,15]

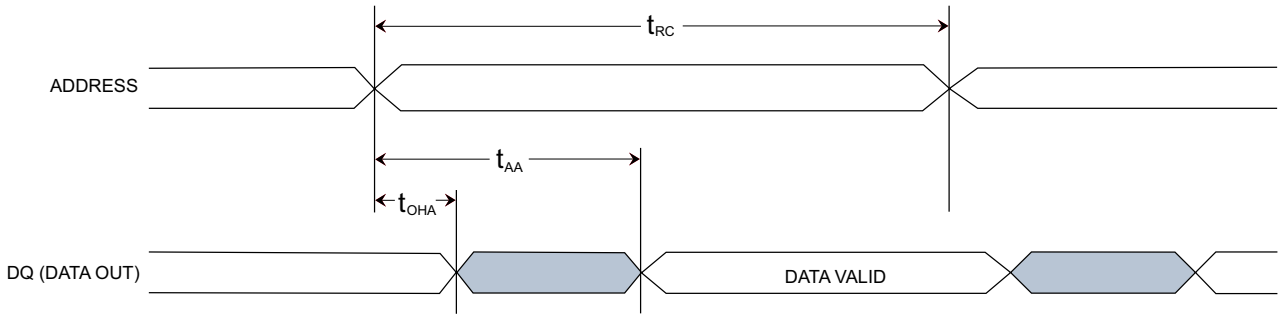
Parameters	Description	15ns		25ns		45ns		Unit
		Min	Max	Min	Max	Min.	Max.	
t_{RC}	STORE/RECALL Initiation Cycle Time	15		25		45		ns
t_{AS}	Address Setup Time	0		0		0		ns
t_{CW}	Clock Pulse Width	12		20		30		ns
t_{GHAX}	Address Hold Time	1		1		1		ns
t_{RECALL}	RECALL Duration		100		100		100	µs
t_{SS} [16,17]	Soft Sequence Processing Time		70		70		70	µs

Hardware STORE Cycle

Parameters	Description	CY14B104L/CY14B104N		Unit
		Min	Max	
t_{DELAY} [18]	Time allowed to complete SRAM Cycle	1	70	µs
t_{HLHX}	Hardware STORE Pulse Width	15		ns

Switching Waveforms

Figure 2. SRAM Read Cycle #1: Address Controlled [8,9,19]



Notes
12. $t_{HRECALL}$ starts from the time V_{CC} rises above V_{SWITCH}.
13. If an SRAM Write has not taken place since the last nonvolatile cycle, no STORE will take place.
14. The software sequence is clocked with $\overline{CE}$ controlled or $\overline{OE}$ controlled reads.
15. The six consecutive addresses must be read in the order listed in the mode selection table. $\overline{WE}$ must be HIGH during all six consecutive cycles.
16. This is the amount of time it takes to take action on a soft sequence command. V_{cc} power must remain HIGH to effectively register command.
17. Commands such as STORE and RECALL lock out IO until operation is complete which further increases this time. See specific command.
18. Read and write cycles in progress before HSB are supplied this amount of time to complete.

Switching Waveforms (continued)

Figure 3. SRAM Read Cycle #2: $\overline{CE}$ and $\overline{OE}$ Controlled [8,19,21]

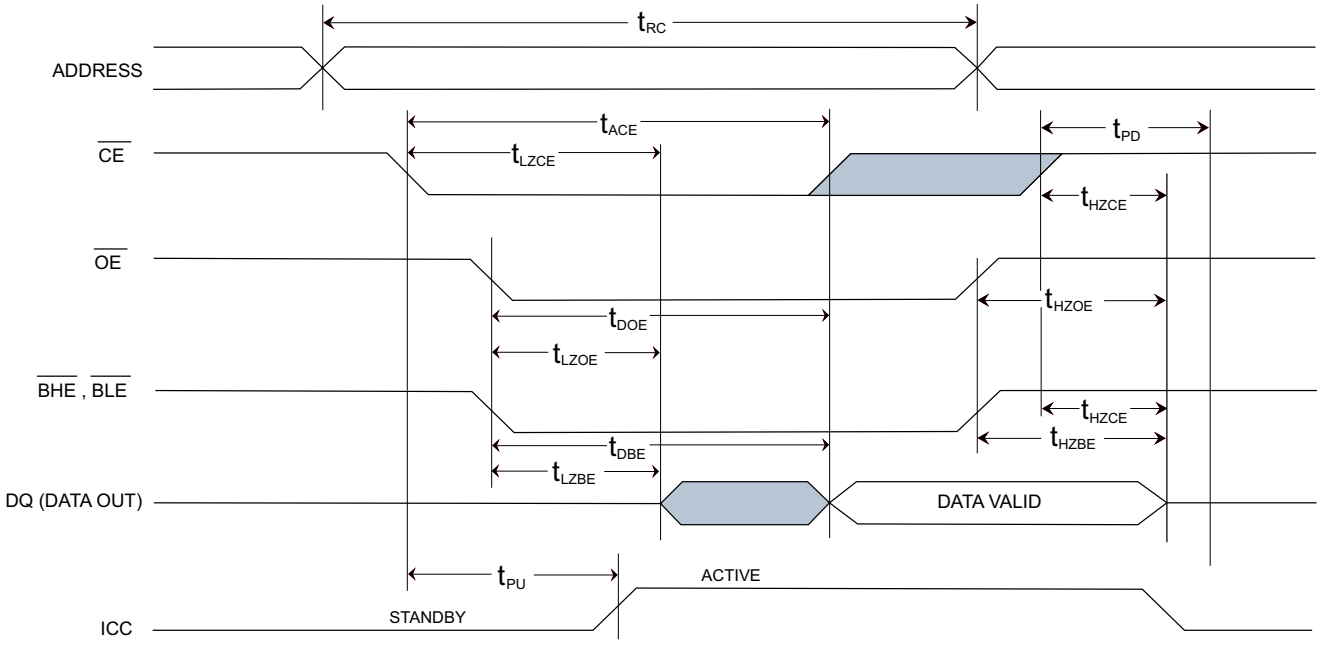
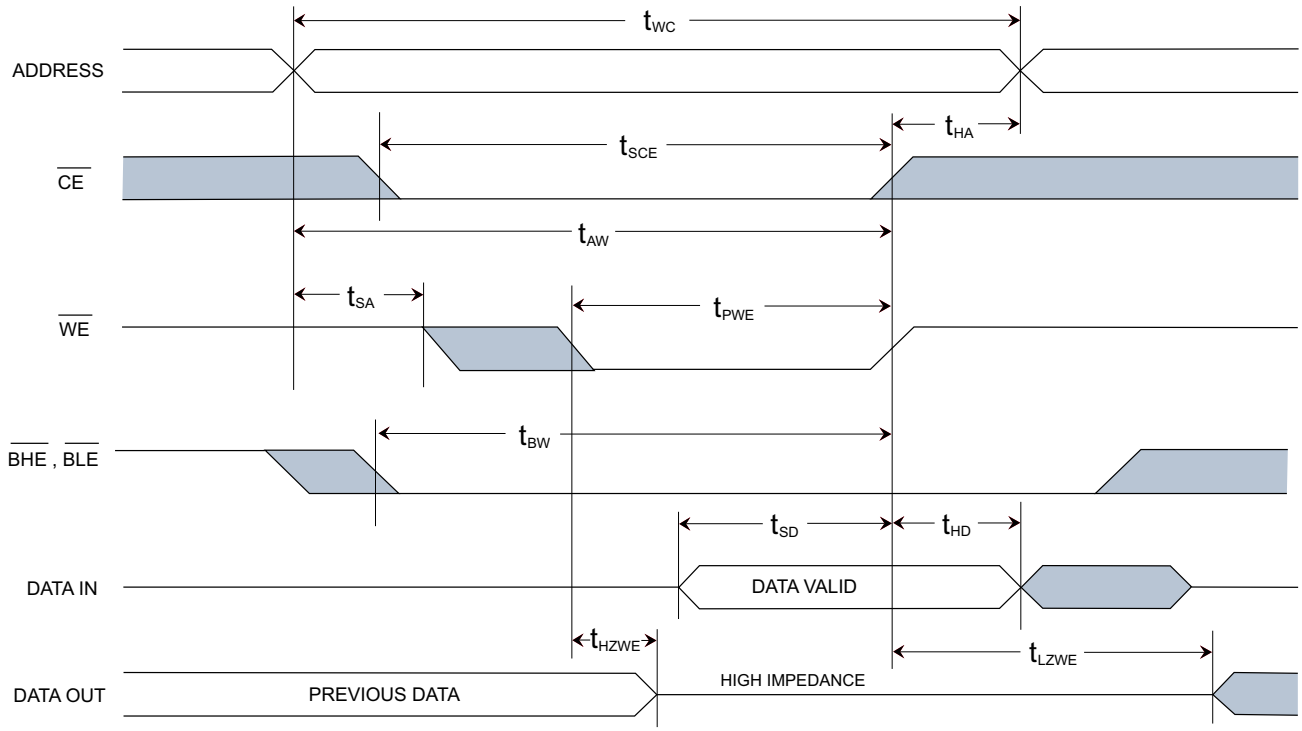


Figure 4. SRAM Write Cycle #1: $\overline{WE}$ Controlled [19,20,21]



Switching Waveforms (continued)

Figure 5. SRAM Write Cycle #2: $\overline{CE}$ Controlled[21]

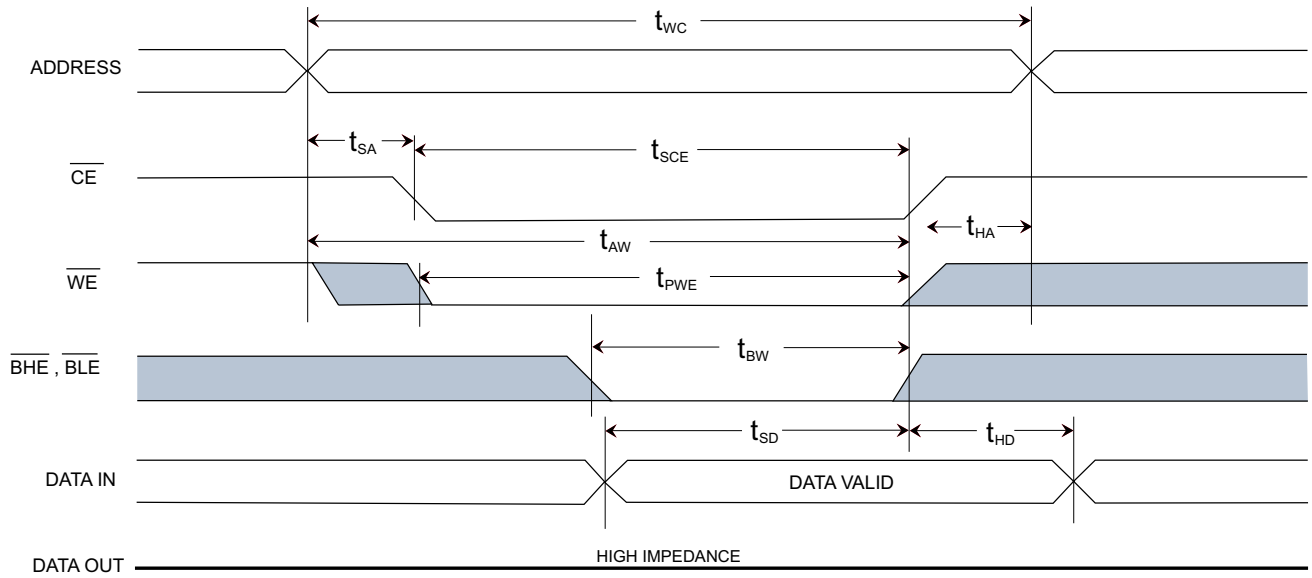
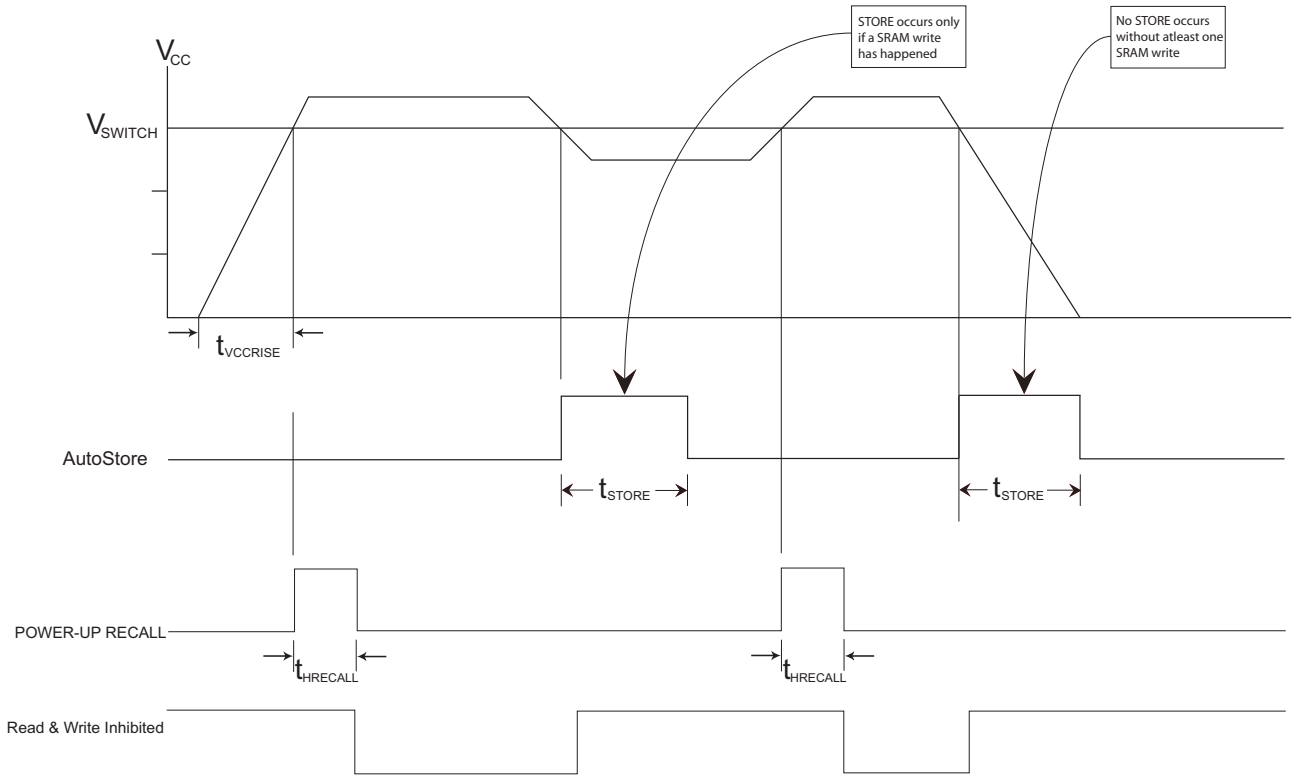


Figure 6. AutoStore/Power Up RECALL



Switching Waveforms (continued)

Figure 7. $\overline{CE}$-controlled Software STORE/RECALL Cycle [15]

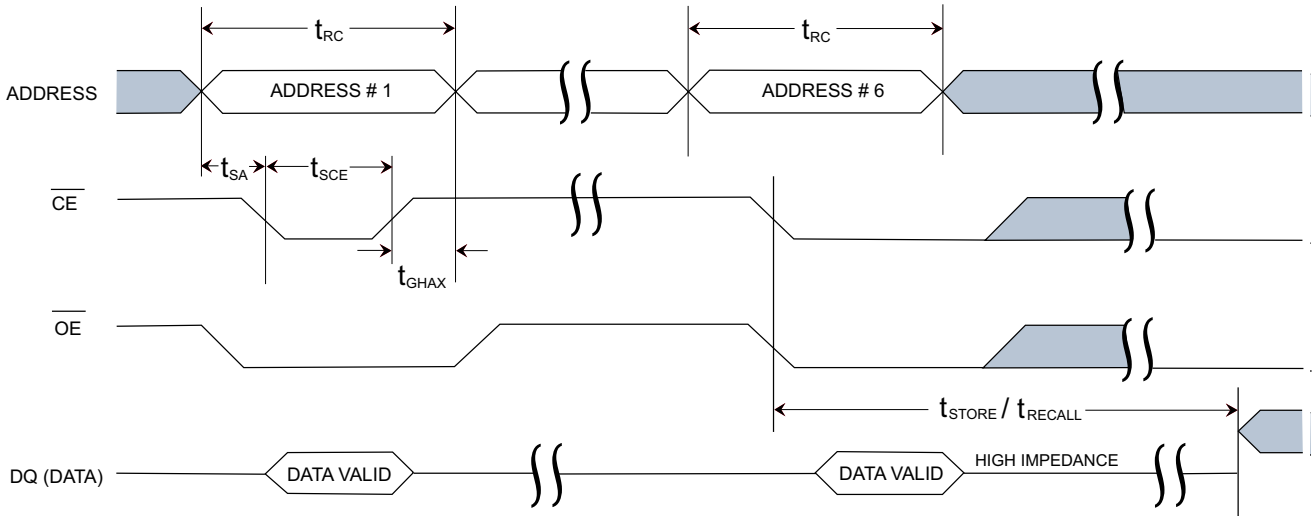
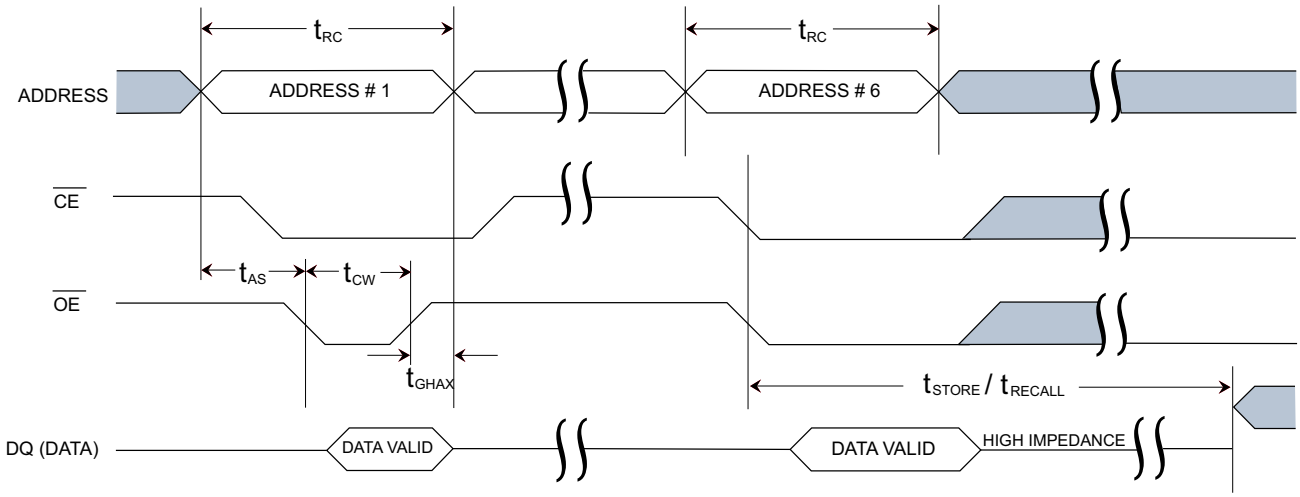


Figure 8. $\overline{OE}$-controlled Software STORE/RECALL Cycle [15]



Switching Waveforms (continued)

Figure 9. Hardware STORE Cycle[18]

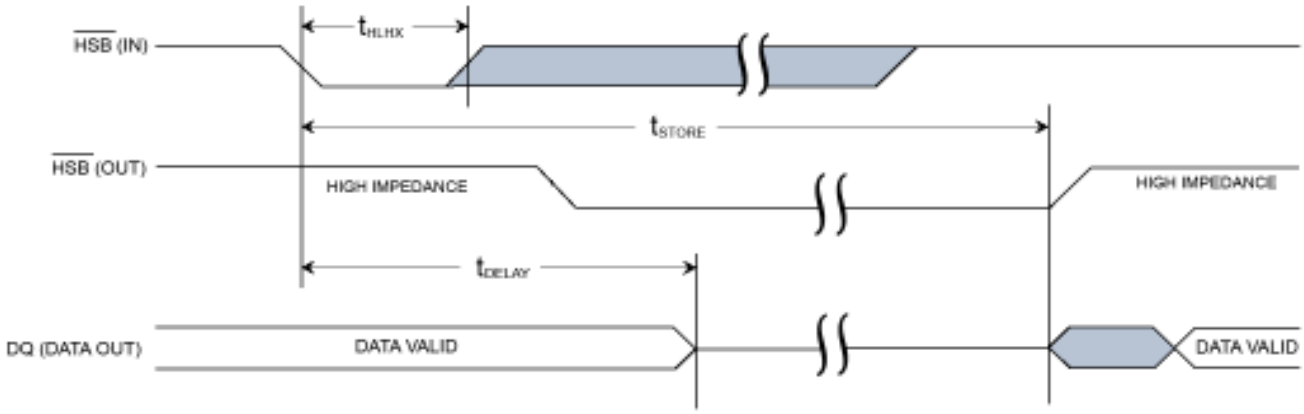
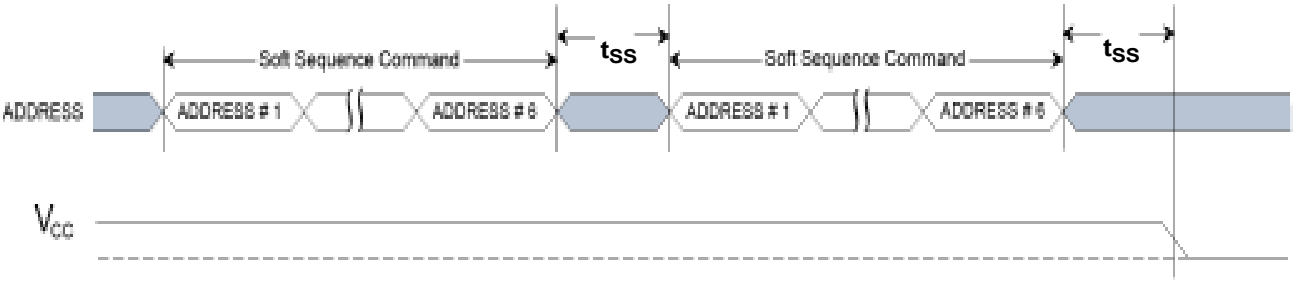


Figure 10. Soft Sequence Processing[16,17]



Ordering Information

Speed (ns)	Ordering Code	Package Diagram	Package Type	Operating Range
15	CY14B104L-ZS15XCT	51-85087	44-pin TSOP II	Commercial
	CY14B104L-ZS15XIT	51-85087	44-pin TSOP II	Industrial
	CY14B104L-ZS15XI	51-85087	44-pin TSOP II	
	CY14B104L-ZSP15XCT	51-85160	54-pin TSOP II	Commercial
	CY14B104L-ZSP15XIT	51-85160	54-pin TSOP II	Industrial
	CY14B104L-ZSP15XI	51-85160	54-pin TSOP II	
	CY14B104N-BA15XCT	51-85128	48-ball FBGA	Commercial
	CY14B104N-BA15XIT	51-85128	48-ball FBGA	Industrial
	CY14B104N-BA15XI	51-85128	48-ball FBGA	
	CY14B104N-ZS15XCT	51-85087	44-pin TSOP II	Commercial
	CY14B104N-ZS15XIT	51-85087	44-pin TSOP II	Industrial
	CY14B104N-ZS15XI	51-85087	44-pin TSOP II	
	CY14B104N-ZSP15XCT	51-85160	54-pin TSOP II	Commercial
	CY14B104N-ZSP15XIT	51-85160	54-pin TSOP II	Industrial
	CY14B104N-ZSP15XI	51-85160	54-pin TSOP II	
25	CY14B104L-ZS25XCT	51-85087	44-pin TSOP II	Commercial
	CY14B104L-ZS25XIT	51-85087	44-pin TSOP II	Industrial
	CY14B104L-ZS25XI	51-85087	44-pin TSOP II	
	CY14B104L-ZSP25XCT	51-85160	54-pin TSOP II	Commercial
	CY14B104L-ZSP25XIT	51-85160	54-pin TSOP II	Industrial
	CY14B104L-ZSP25XI	51-85160	54-pin TSOP II	
	CY14B104N-BA25XCT	51-85128	48-ball FBGA	Commercial
	CY14B104N-BA25XIT	51-85128	48-ball FBGA	Industrial
	CY14B104N-BA25XI	51-85128	48-ball FBGA	
	CY14B104N-ZS25XCT	51-85087	44-pin TSOP II	Commercial
	CY14B104N-ZS25XIT	51-85087	44-pin TSOP II	Industrial
	CY14B104N-ZS25XI	51-85087	44-pin TSOP II	
	CY14B104N-ZSP25XCT	51-85160	54-pin TSOP II	Commercial
	CY14B104N-ZSP25XIT	51-85160	54-pin TSOP II	Industrial
	CY14B104N-ZSP25XI	51-85160	54-pin TSOP II	

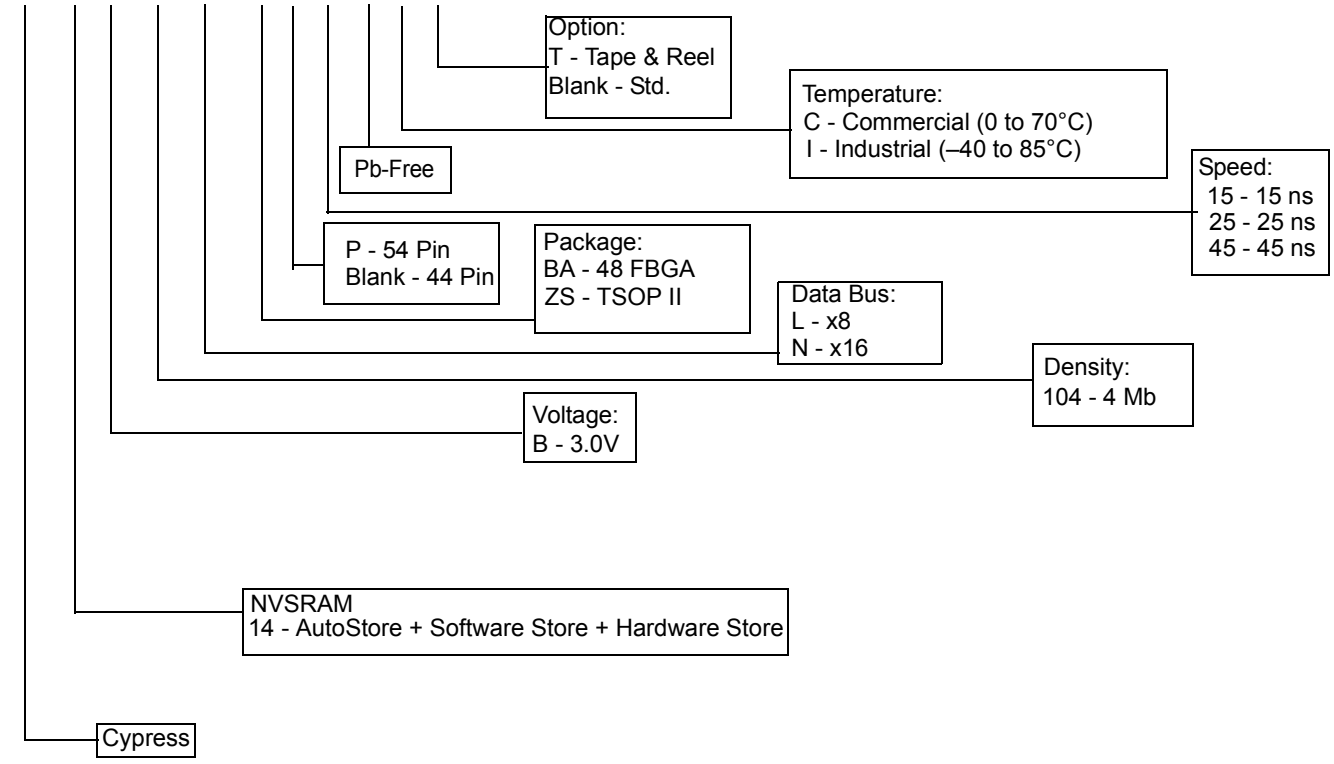
Notes
19. $\overline{HSB}$ must remain HIGH during READ and WRITE cycles.
20. $\overline{CE}$ or $\overline{WE}$ must be $\geq V_{IH}$ during address transitions.
21. $\overline{BHE}$ and $\overline{BLE}$ are applicable for x16 configuration only.

Ordering Information (continued)

Speed (ns)	Ordering Code	Package Diagram	Package Type	Operating Range
45	CY14B104L-BV45XCT	51-85128	48-ball FBGA	Commercial
	CY14B104L-BV45XIT	51-85128	48-ball FBGA	Industrial
	CY14B104L-BV45XI	51-85128	48-ball FBGA	
	CY14B104L-ZS45XCT	51-85087	44-pin TSOP II	Commercial
	CY14B104L-ZS45XIT	51-85087	44-pin TSOP II	Industrial
	CY14B104L-ZS45XI	51-85087	44-pin TSOP II	
	CY14B104L-ZSP45XCT	51-85160	54-pin TSOP II	Commercial
	CY14B104L-ZSP45XIT	51-85160	54-pin TSOP II	Industrial
	CY14B104L-ZSP45XI	51-85160	54-pin TSOP II	
	CY14B104N-BV45XCT	51-85128	48-ball FBGA	Commercial
	CY14B104N-BV45XIT	51-85128	48-ball FBGA	Industrial
	CY14B104N-BV45XI	51-85128	48-ball FBGA	
	CY14B104N-ZS45XCT	51-85087	44-pin TSOP II	Commercial
	CY14B104N-ZS45XIT	51-85087	44-pin TSOP II	Industrial
	CY14B104N-ZS45XI	51-85087	44-pin TSOP II	
	CY14B104N-ZSP45XCT	51-85160	54-pin TSOP II	Commercial
	CY14B104N-ZSP45XIT	51-85160	54-pin TSOP II	Industrial
	CY14B104N-ZSP45XI	51-85160	54-pin TSOP II	

PART NUMBERING NOMENCLATURE

CY 14 B 104 L - ZS P 15 X C T



Package Diagrams

Figure 11. 54-pin TSOP II (51-85160)

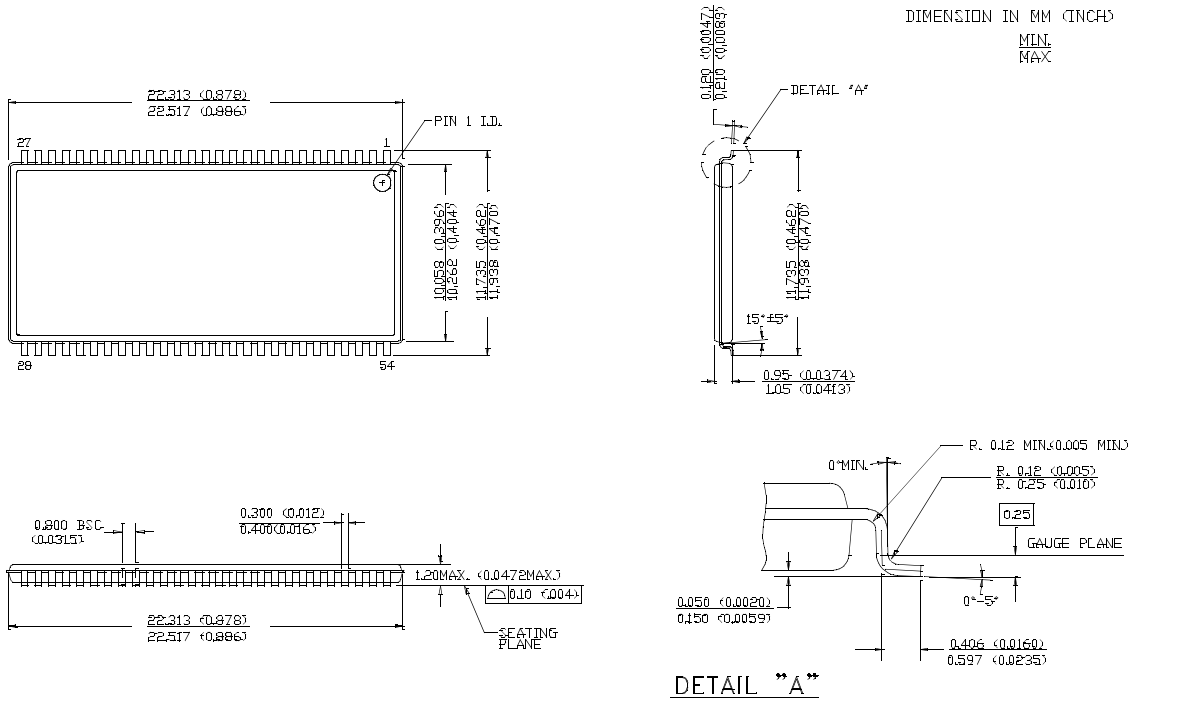
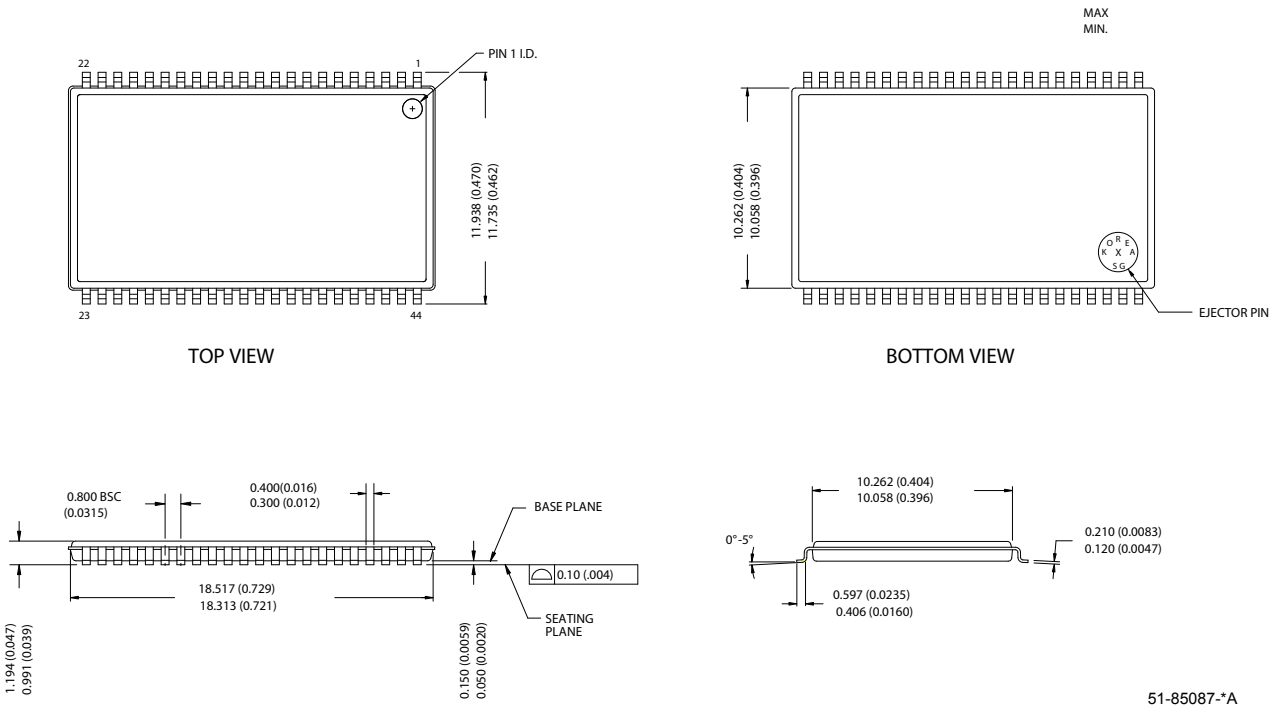
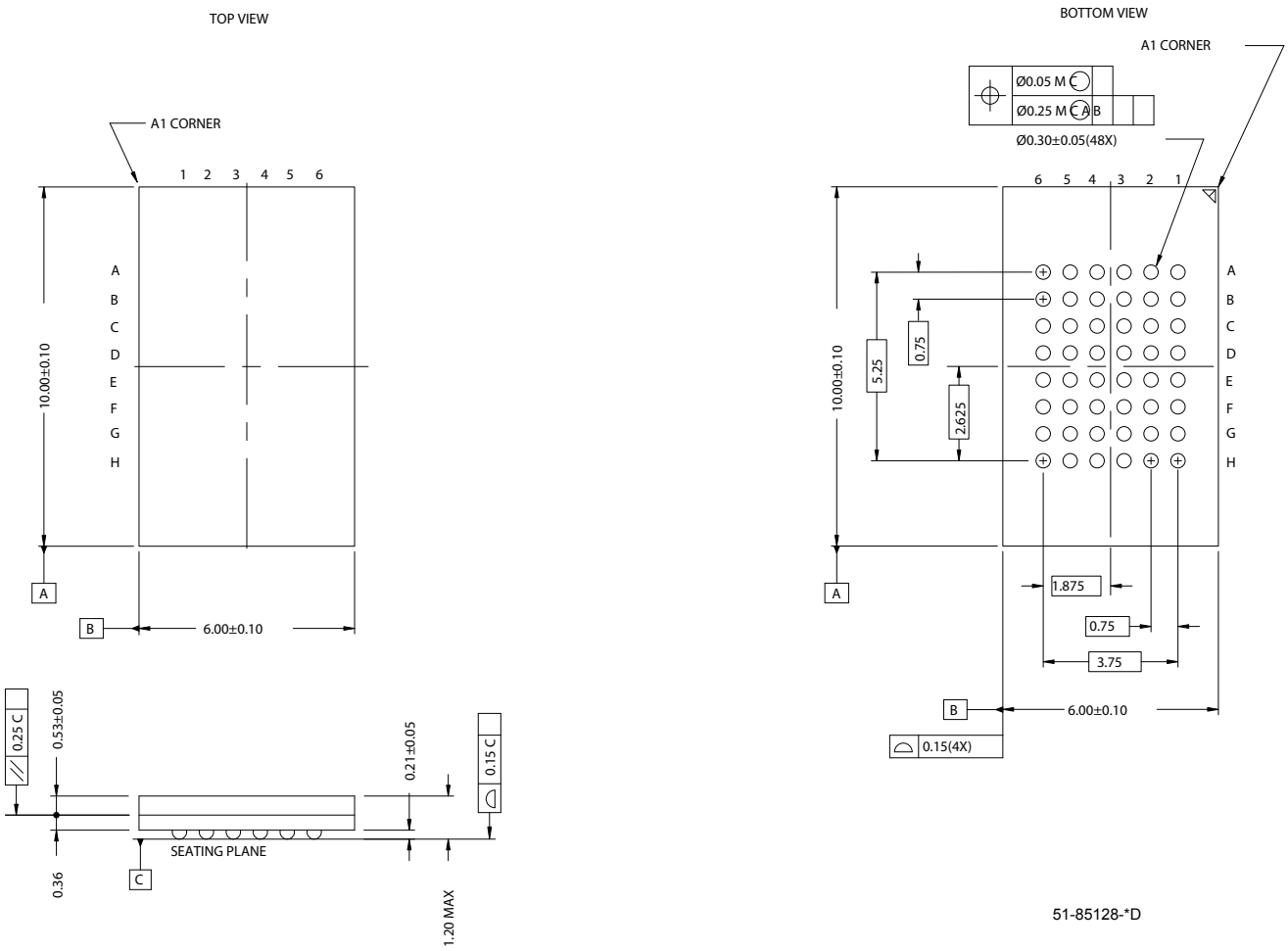


Figure 12. 44-Pin TSOP II (51-85087)



Package Diagrams (continued)

Figure 13. 48-ball FBGA (6 mm x 10 mm x 1.2 mm)



Document History Page

Document Title: CY14B104L/CY14B104N 1-Mbit (128K x 8) nvSRAM Document Number: 001-07102				
REV.	**ECN NO.**	**Issue Date**	**Orig. of Change**	**Description of Change**
**	431039	See ECN	TUP	New Data Sheet
*A	489096	See ECN	TUP	Removed 48 SSOP Package Added 48 FBGA and 54 TSOPII Packages Updated Part Numbering Nomenclature and Ordering Information Added Soft Sequence Processing Time Waveform
*B	499597	See ECN	PCI	Removed 35 ns speed bin Added 55 ns speed bin. Updated AC table for the same Changed “Unlimited” read/write to “infinite” read/write Features section: Changed typical I_{CC} at 200-ns cycle time to 8 mA Changed STORE cycles from 500K to 200K cycles Shaded Commercial grade in operating range table Modified Icc/Isb specs 48 FBGA package nomenclature changed from BW to BV Modified part nomenclature table. Changes reflected in the ordering information table
*C	517793	See ECN	TUP	Removed 55ns speed bin Changed pinout for 44TSOPII and 54TSOPII packages Changed I_{SB} to 1mA Changed I_{CC4} to 3mA Changed V_{CAP} min to 35µF Changed V_{IH} max to Vcc + 0.5V Changed t_{STORE} to 15ms Changed t_{PWE} to 10ns Changed t_{SCE} to 15ns Changed t_{SD} to 5ns Changed t_{AW} to 10ns Removed t_{HLBL} Added Timing Parameters for $\overline{BHE}$ and $\overline{BLE}$ - t_{DBE}, t_{LZBE}, t_{HZBE}, t_{BW} Removed min specification for Vswitch Changed t_{GLAX} to 1ns Added t_{DELAY} max of 70us Changed t_{SS} specification from 70us min to 70us max
*D	774001	See ECN	UHA	Changed the datasheet from Advance information to Preliminary 48 FBGA package code changed from BV to BA Removed 48 FBGA package in X8 configuration in ordering information. Changed t_{DBE} to 10ns in 15ns part Changed t_{HZBE} in 15ns part to 7ns and in 25ns part to10ns Changed t_{BW} in 15ns part to 15ns and in 25ns part to 20ns Changed t_{GLAX} to t_{GHAX} Changed the value of I_{CC3} to 25mA Changed the value of t_{AW} in 15ns part to15ns Changed A_{18} and A_{19} Pins in FBGA Pin Configuration to NC
*E	914220	See ECN	UHA	Included all the information for 45ns part in this datasheet